

PRODUCT CHARACTERISTICS

V_{DSS}	110V
$R_{DS(ON)}$ Typ(@ $V_{GS}=10V$)	1.5m Ω
Qg@typ	142nC
I_D	373A

APPLICATIONS

- * Battery Management
- * Motor Control and Drive
- * Switching Applications

FEATURE

- * Low Gate Charge
- * Low Reverse Transfer Capacitance
- * 100% Avalanche Tested

ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT1116N	TO-247	30 pieces/Tube

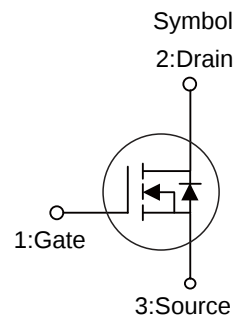
ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	110	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current Continuous(@ $V_{GS}=10V, T_A=25^{\circ}C$)	I_D	373	A
Drain Current Continuous(@ $V_{GS}=10V, T_A=100^{\circ}C$)	I_D	263	A
Drain Current Pulsed	I_{DM}	1492	A
Avalanche Energy *	E_{AS}	3400	mJ
Power Dissipation	P_D	440	W
Junction Temperature	T_J	+175	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +175	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Ambient	R_{thJA}	32.8	$^{\circ}C/W$
Junction to Case	R_{thJC}	0.34	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C, V_{DD}=70V, V_G=10V, L=1mH, R_g=25\Omega$



TO-247

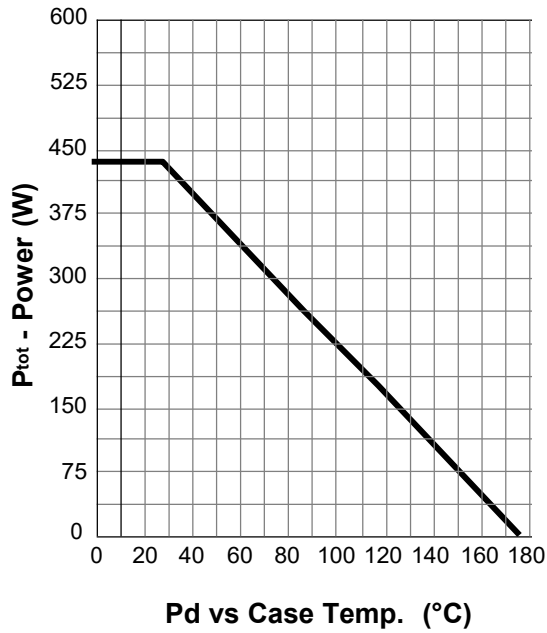


■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

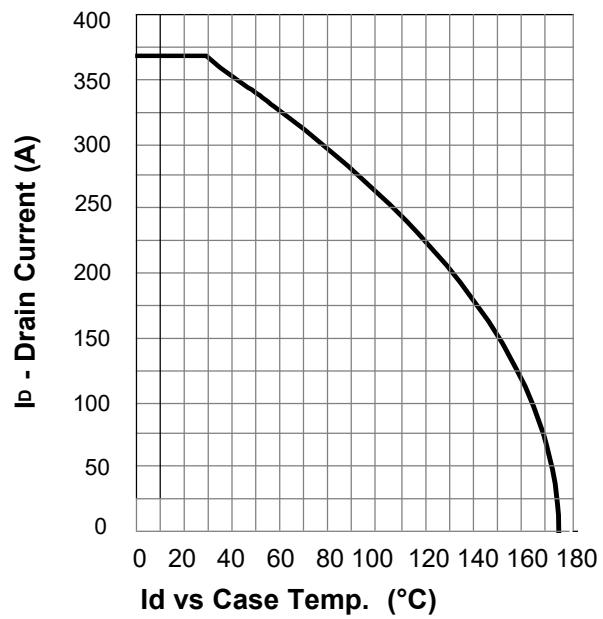
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V, I _D =250μA	110	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{DS} =0V, V _{GS} =+20V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{DS} =0V, V _{GS} =-20V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	1.5	1.8	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2	-	4	V
Dynamic characteristics						
Gate capacitance	R _g	V _{GS} =0V, V _{DS} =0V ,f=1.0MHz	-	1.3	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =5A	-	25	-	S
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V f=1.0MHz	-	12700	-	pF
Output Capacitance	C _{oss}		-	3400	-	pF
Reverse Transfer Capacitance	C _{rss}		-	137	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	I _D =50A, V _{DS} =50V R _G =4.5 Ω ,V _{GS} =10V	-	36	-	ns
Rise Time	t _r		-	119	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	138	-	ns
Fall Time	t _f		-	120	-	ns
Total Gate Charge	Q _g	I _D =50A, V _{DS} =50V V _{GS} =10V	-	142	-	nC
Gate to Source Charge	Q _{gs}		-	59	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	48	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	373	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	1492	A
Diode Forward Voltage	V _{SD}	I _{SD} =50 A, V _{GS} =0V	-	-	1.3	V
Reverse Recovery Time	t _{rr}	I _{SD} =50A, T _J =25 °C	-	109	-	ns
Reverse Recovery Charge	Q _{rr}	dI /dt=100A/μs	-	294	-	nC

■ TYPICAL CHARACTERISTICS

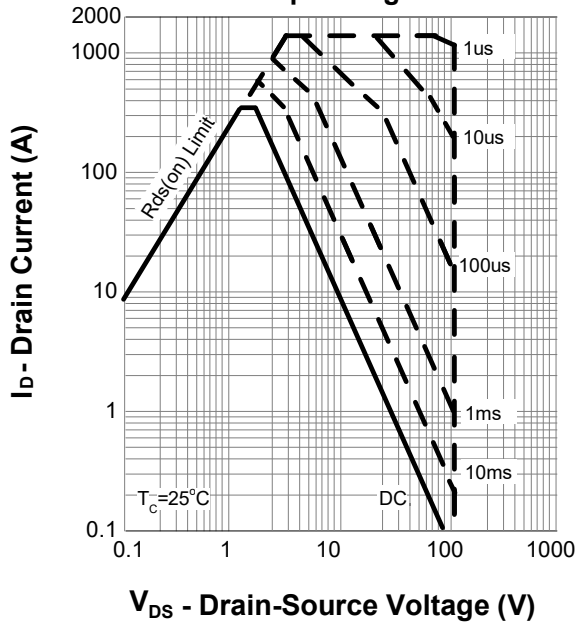
Power Capability



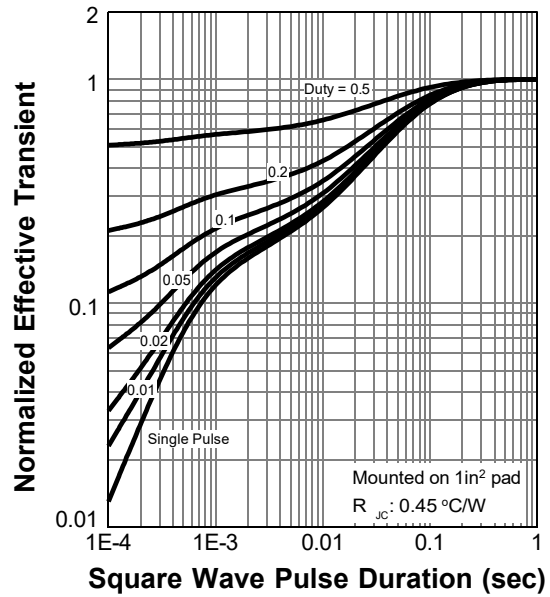
Current Capability



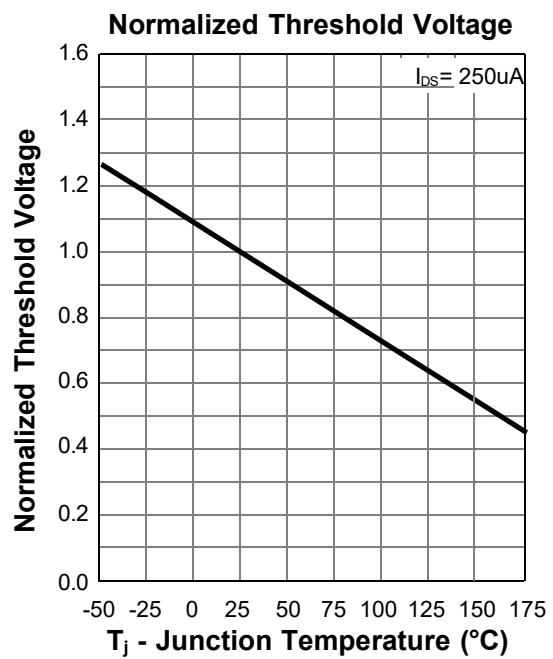
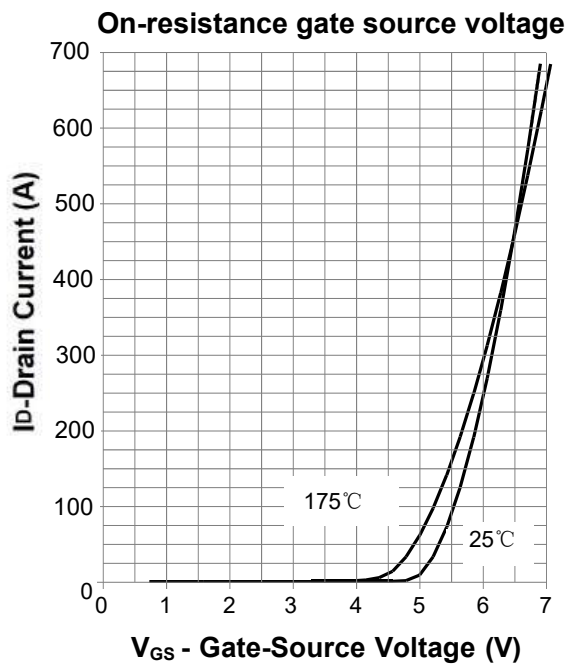
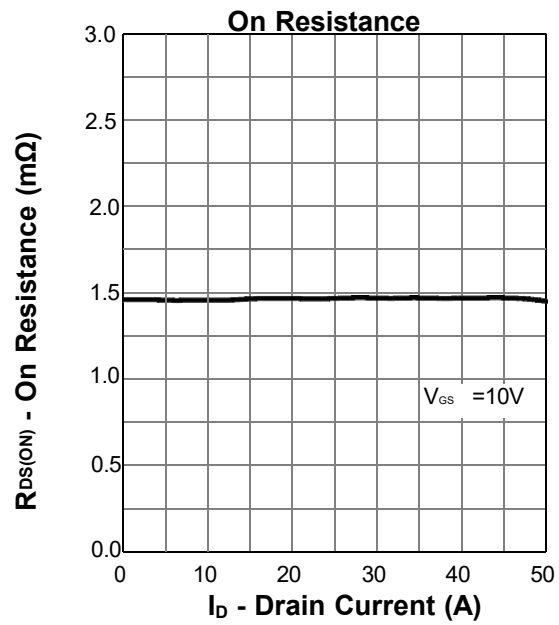
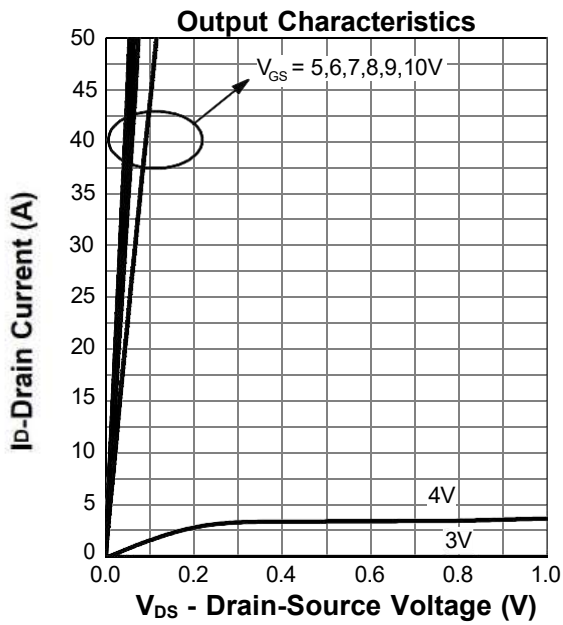
Safe Operating Area



Transient Thermal Impedance



■ TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)

